

IN THE SPECIFICATION

Page 6, paragraph [0020]:

[0020] The first etch/dep ratio is selected to be higher than the second etch/dep ratio. Thus, the first layer of trench filling material 20 is etched at a higher rate than the second layer of trench filling material 22. The first and second etch/dep ratios may be controlled in a number of suitable manners. For example, the first gas flow rate may be selected to be lower than the second gas flow rate. It will be understood by those having skill in the art that as the flow rate of the gas flow is increased the deposition rate will also increase. The first RF bias may be selected to be higher than the second RF bias. It will be understood that increasing the RF bias increases the rate at which the fill is etched. Thus, both the gas flow and the RF bias may be adjusted in order to control the etch/dep ratio. Generally, the first flow rate is selected to be lower than the second gas flow rate. Additionally, the first RF bias is generally selected to provide a relatively high rate of etch, and the second RF bias is selected to give a relatively low rate of etch for the given gas flows. For example, the first etch/dep ratio may be above about ~~[[0.03]]~~ 0.3, and the second etch/dep ratio may be below about ~~[[0.03]]~~ 0.3. However, it will be understood that the preferred etch/dep ratio is process dependent.